LISTING OF CLAIMS:

The following listing of claims replaces all previous versions and listings of claims in the present application.

1. - 12. (Canceled)

13. (Currently amended) A method of manufacturing a ~~microactuator~~micromechanical structure, comprising the steps of

forming a stationary element having a stationary element electrode and a movable element having a movable element electrode on a semiconductor substrate, said movable element being formed to be separated from a surface of said semiconductor substrate and movable in a direction parallel to said surface of said semiconductor substrate; and

forming a microstructure on said movable element and ~~at least one of~~ opposing surfaces of ~~one of~~ said stationary element ~~and said substrate~~.

14. (Original) A method according to claim 13, wherein the step of forming said microstructure comprises the step of forming a polysilicon thin film on said movable element and at least one of said opposing surfaces of one of said stationary element and said substrate to form a microstructural shape on a surface of said polysilicon thin film.

15. (Original) A method according to claim 13, wherein the step of forming said microstructure comprises the step of etching said movable element and at least one of said

opposing surfaces of one of said stationary element and said substrate to form a microstructural shape.

16. (New) A method of manufacturing a micromechanical structure, said micromechanical structure comprising:

a substrate on which an insulation film is at least partly formed;

a stationary element fixed on said insulating film of said substrate, and having a plurality of stationary element electrodes arranged at a predetermined pitch;

a movable element supported above said substrate by a spring member, said movable element having a plurality of movable element electrodes interdigitized with said stationary element electrodes, said movable element movable in a direction parallel to a surface of said substrate, wherein said stationary element and said movable element each have respective opposing surfaces which are substantially perpendicular to said surface of said substrate; and

a microstructure formed on at least one of said opposing surfaces of said movable element and said stationary element,

said method comprising:

etching a semiconductor layer formed on said substrate to define a structure of said stationary element and said movable element,

wherein said etching includes forming said microstructure on at least one of said opposing surfaces of said movable element and said stationary element.

17. (New) A method according to claim 16, wherein at least a surface of said stationary element and movable element is formed of polysilicon, and wherein said etching etches said polysilicon.

18. (New) A method according to claim 16, wherein the forming said microstructure further comprises forming a polysilicon thin film on said movable element and at least one of said opposing surfaces of one of said stationary element and said substrate to form a microstructural shape on a surface of said polysilicon thin film.

19. (New) A method according to claim 16, wherein the forming said microstructure comprises etching said movable element and at least one of said opposing surfaces of one of said stationary element and said substrate to form a microstructural shape.